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Attorney Docket # 170-2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of )

Hayakawa et al. )

Serial No.: 09/532,915 )

Filed: March 22, 2000 )

For: Semiconductor Device and Method )  
of Manufacturing The Same )

Art Unit: 2826 )

Examiner: Sefer, A. )

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Commissioner for Patents  
Washington, D.C. 20231

February 11, 2002

AMENDMENT B

Sir:

In response to the Office Action mailed October 10, 2001 setting a three-month term for response. A one month extension of time is requested, which extends the time to February 10, which is automatically carried forward to Monday, February 11, 2002. Applicants request amendment of the application as follows:

IN THE CLAIMS:

Please add the following new claims 18 to 57:

-- 18. A semiconductor device comprising:

an insulating underlying film provided over a substrate and comprising at least a silicon oxide nitride film and an insulting layer containing silicon and oxygen;

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